

SEMICONDUCTOR DICE

MOSFETs — N-CHANNEL

ZETEX SEMICONDUCTORS

Dice type	BV_{DSS}	$R_{DS(on)}$			Max. I_{DSS} at Rated V_{DS}	Max. I_{GSS} at $V_{GS}=20V$	$I_{D(on)}$			$V_{GS(th)}$			Chip geometry at
	Min.	Max. at I_D	V_{GS}	V_{GS}			Min. at V_{DS}	V_{GS}	V_{GS}	Min.	Max. at I_D	at	
	Volts	Ω	A	Volts	μA	nA	A	Volts	Volts	Volts	Volts	mA	
ZVN0540	400	50	0.1	10	10	20	0.15	25	10	1.0	3.0	1.0	G18
ZVNL535	350	40	0.1	5	50	100	0.20	25	5	0.5	1.5	1.0	G18
ZVN2535	350	35	0.1	10	10	20	0.25	25	10	1.0	3.0	1.0	G18
ZVN0124	240	16	0.25	10	10	20	0.5	25	10	1.0	3.0	1.0	G17
ZVNL120	200	10	0.25	5	10	100	0.5	25	5	0.5	1.5	1.0	G17
ZVN2120	200	10	0.25	10	10	20	0.5	25	10	1.0	3.0	1.0	G17
ZVN3320	200	25	0.1	10	10	100	0.25	25	10	1.0	3.0	1.0	G21
ZVN2110	100	4.0	1.0	10	1	20	1.5	25	10	0.8	2.4	1.0	G17
ZVN3310	100	10.0	0.5	10	1	20	0.5	25	10	0.8	2.4	1.0	G21
ZVN1409	90	250.0	0.005	10	1	100	0.01	25	10	0.8	2.4	0.1	G20
ZVN2106	60	2.0	1.0	10	0.5	20	2.0	18	10	0.8	2.4	1.0	G17
ZVN4106	60	5.0	0.2	5	10	100	1.0	25	10	1.3	3.0	1.0	G19
ZVN3306	60	5.0	0.5	10	0.5	20	0.75	18	10	0.8	2.4	1.0	G21
VN10L	60	7.5	0.2	5	10	100	0.75	15	10	0.8	2.5	1.0	G21

MOSFETs — P-CHANNEL

Dice type	BV_{DSS}	$R_{DS(on)}$			Max. I_{DSS} at Rated V_{DS}	Max. I_{GSS} at $V_{GS}=20V$	$I_{D(on)}$			$V_{GS(th)}$			Chip geometry at
	Min.	Max. at I_D	V_{GS}	V_{GS}			Min. at V_{DS}	V_{GS}	V_{GS}	Min.	Max. at I_D	at	
	Volts	Ω	A	Volts	μA	nA	A	Volts	Volts	Volts	Volts	mA	
ZVP0540	-400	150	-50	-10	-20	-20	-0.1	-25	-10	-1.5	-4.5	-1.0	G22
ZVP0535	-350	100	-50	-10	-20	-100	-0.12	-25	-10	-1.5	-4.5	-1.0	G22
ZVP2120	-200	25	-150	-10	-10	-20	-0.3	-25	-10	-1.5	-3.5	-1.0	G17
ZVP1320	-200	80	-50	-10	-10	-20	-0.1	-25	-10	-1.5	-3.5	-1.0	G21
ZVP2110	-100	8	-375	-10	-1	-20	-0.75	-25	-10	-1.5	-3.5	-1.0	G17
ZVP3310	-100	20	-150	-10	-1	-20	-0.3	-25	-10	-1.5	-3.5	-1.0	G21
ZVP2106	-60	5	-500	-10	-0.5	-20	-1.0	-18	-10	-1.5	-3.5	-1.0	G17
ZVP3306	-60	14	-200	-10	-0.5	-20	-0.4	-18	-10	-1.5	-3.5	-1.0	G21